

Silicon Carbide (SiC) MOSFET – EliteSiC, 33 mohm, 650 V, M2, TOLL

NTBL045N065SC1

Features

- Typ. $R_{DS(on)}$ = 33 m Ω @ V_{GS} = 18 V
Typ. $R_{DS(on)}$ = 45 m Ω @ V_{GS} = 15 V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 105 nC)
- Low Effective Output Capacitance (C_{oss} = 162 pF)
- 100% Avalanche Tested
- T_J = 175°C
- RoHS Compliant

Typical Applications

- SMPS (Switching Mode Power Supplies)
- Solar Inverters
- UPS (Uninterruptable Power Supplies)
- Energy Storage

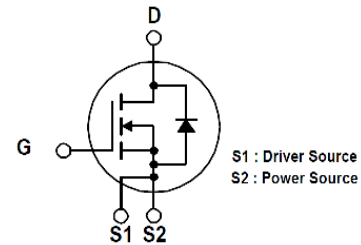
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	650	V	
Gate-to-Source Voltage		V_{GS}	-8/+22	V	
Recommended Operation Values of Gate – Source Voltage		$T_C < 175^\circ\text{C}$ V_{GSop}	-5/+18	V	
Continuous Drain Current (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	I_D	73	A
			P_D	348	W
Continuous Drain Current (Notes 1, 2)	Steady State	$T_C = 100^\circ\text{C}$	I_D	51	A
			P_D	174	W
Pulsed Drain Current (Note 3)		$T_C = 25^\circ\text{C}$	I_{DM}	182	A
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C	
Source Current (Body Diode)		I_S	75	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 12 \text{ A}_{pk}$, $L = 1 \text{ mH}$) (Note 4)		E_{AS}	72	mJ	
Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		T_L	260	°C	

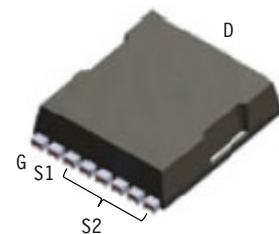
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on a FR-4 board using 1 in 2 pad of 2 oz copper.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
3. Repetitive rating, limited by max junction temperature.
4. E_{AS} of 72 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 1 \text{ mH}$, $I_{AS} = 12 \text{ A}$, $V_{DD} = 50 \text{ V}$, $V_{GS} = 18 \text{ V}$.

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	50 m Ω @ 18 V	73 A

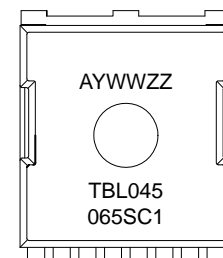


N-Channel MOSFET



H-PSOF8L
CASE 100DC

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code
- TBL045065SC1 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Units
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	0.43	°C/W
Junction-to-Ambient – Steady State (Notes 1, 2)	$R_{\theta JA}$	43	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 20\text{ mA}$, refer to 25°C		0.15		V/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$ $V_{DS} = 650\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 175^\circ\text{C}$		1	mA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = +18/-5\text{ V}, V_{DS} = 0\text{ V}$			250	nA

ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 8\text{ mA}$	1.8	2.8	4.3	V
Recommended Gate Voltage	V_{GOP}		-5		+18	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 15\text{ V}, I_D = 25\text{ A}, T_J = 25^\circ\text{C}$		45		m Ω
		$V_{GS} = 18\text{ V}, I_D = 25\text{ A}, T_J = 25^\circ\text{C}$		33	50	
		$V_{GS} = 18\text{ V}, I_D = 25\text{ A}, T_J = 175^\circ\text{C}$		40		
Forward Transconductance	g_{FS}	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$		16		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz},$ $V_{DS} = 325\text{ V}$		1870		pF
Output Capacitance	C_{OSS}			162		
Reverse Transfer Capacitance	C_{RSS}			14		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/18\text{ V}, V_{DS} = 520\text{ V},$ $I_D = 25\text{ A}$		105		nC
Gate-to-Source Charge	Q_{GS}			27		
Gate-to-Drain Charge	Q_{GD}			30		
Gate-Resistance	R_G	$f = 1\text{ MHz}$		3.1		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/18\text{ V}, V_{DS} = 400\text{ V},$ $I_D = 25\text{ A}, R_G = 2.2\ \Omega,$ Inductive Load		13		ns
Rise Time	t_r			14		
Turn-Off Delay Time	$t_{d(OFF)}$			26		
Fall Time	t_f			7		μJ
Turn-On Switching Loss	E_{ON}			47		
Turn-Off Switching Loss	E_{OFF}			33		
Total Switching Loss	E_{TOT}			80		

SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Source-Drain Diode Forward Current	I_{SD}	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$			75	A
Pulsed Source-Drain Diode Forward Current (Note 3)	I_{SDM}	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$			182	A
Forward Diode Voltage	V_{SD}	$V_{GS} = -5\text{ V}, I_{SD} = 25\text{ A}, T_J = 25^\circ\text{C}$		4.4		V

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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SOURCE-DRAIN DIODE CHARACTERISTICS

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
Reverse Recovery Time	t_{RR}	$V_{GS} = -5/18\text{ V}$, $I_{SD} = 25\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$		20		ns	
Reverse Recovery Charge	Q_{RR}			108		nC	
Reverse Recovery Energy	E_{REC}			4.5		μJ	
Peak Reverse Recovery Current	I_{RRM}			11		A	
Charge time	T_a				11		ns
Discharge time	T_b				8.5		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

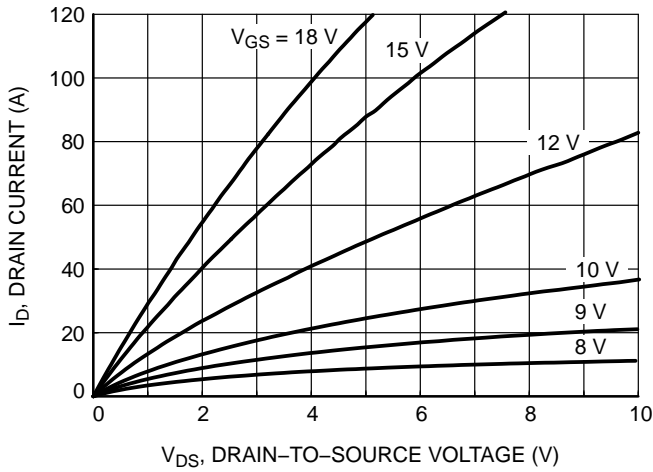


Figure 1. On-Region Characteristics

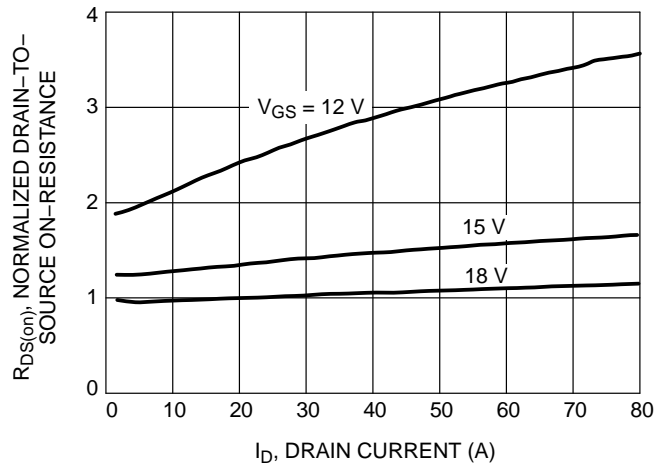


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

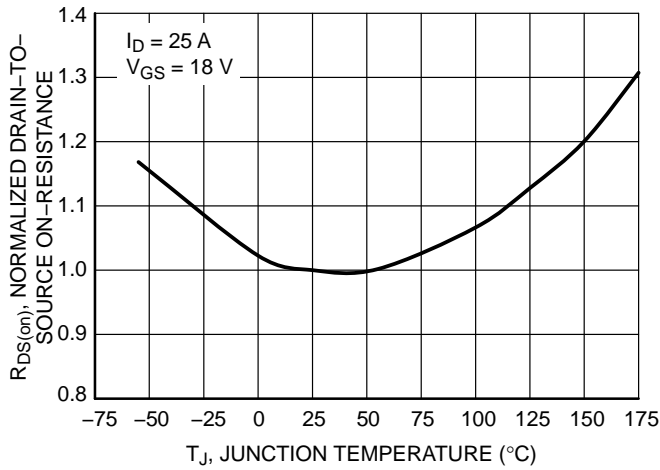


Figure 3. On-Resistance Variation with Temperature

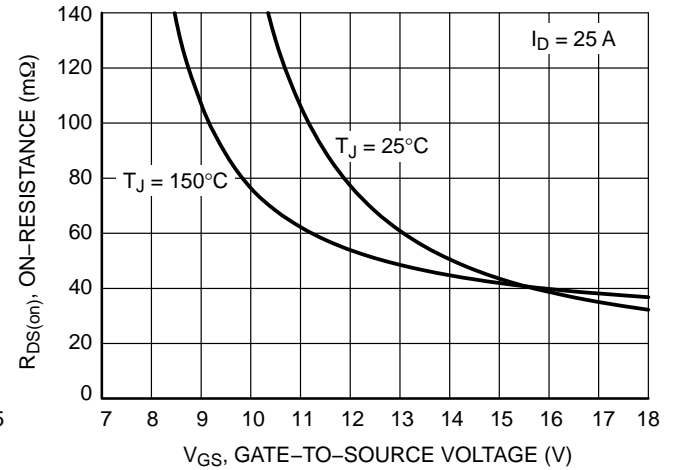


Figure 4. On-Resistance vs. Gate-to-Source Voltage

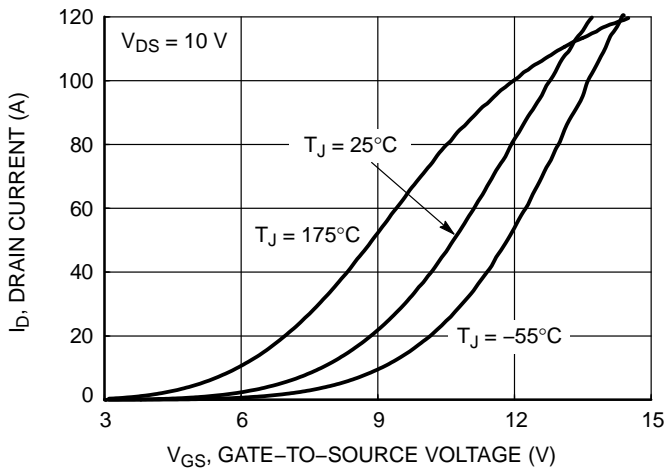


Figure 5. Transfer Characteristics

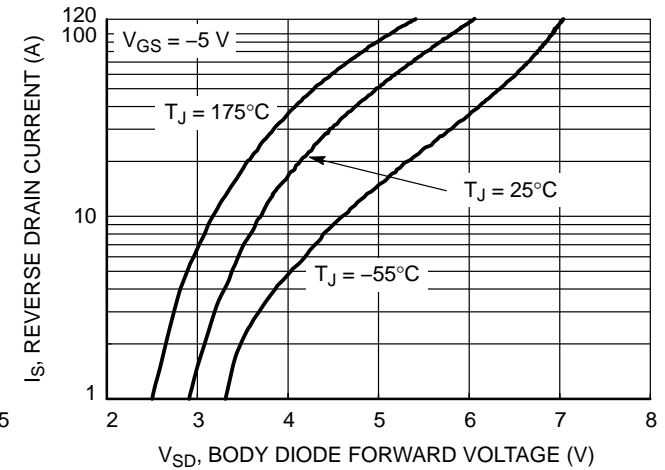


Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

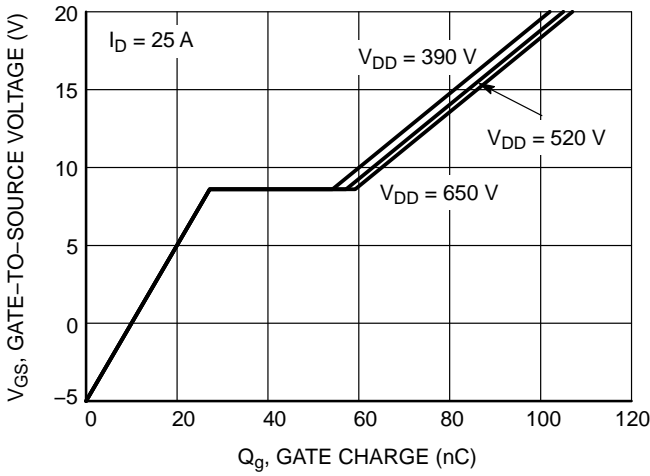


Figure 7. Gate-to-Source Voltage vs. Total Charge

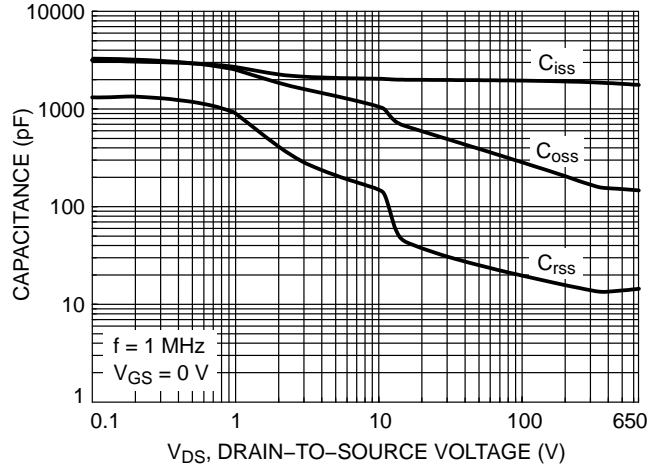


Figure 8. Capacitance vs. Drain-to-Source Voltage

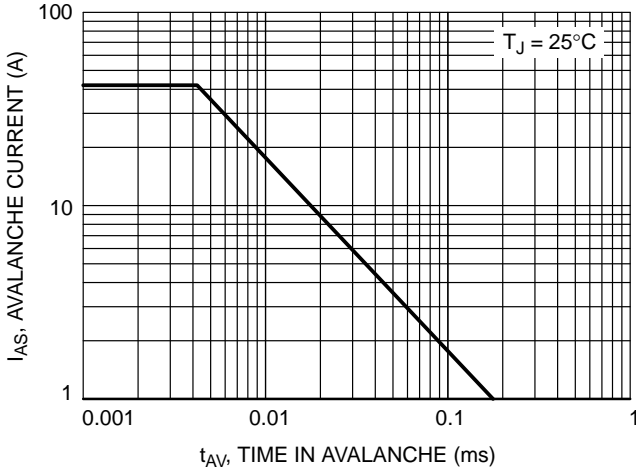


Figure 9. Unclamped Inductive Switching Capability

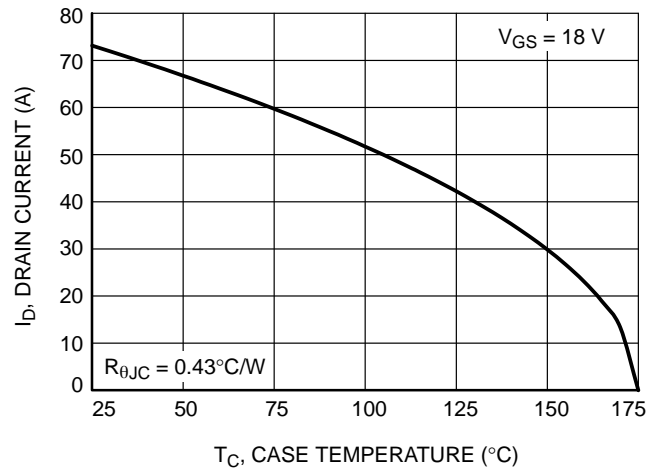


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

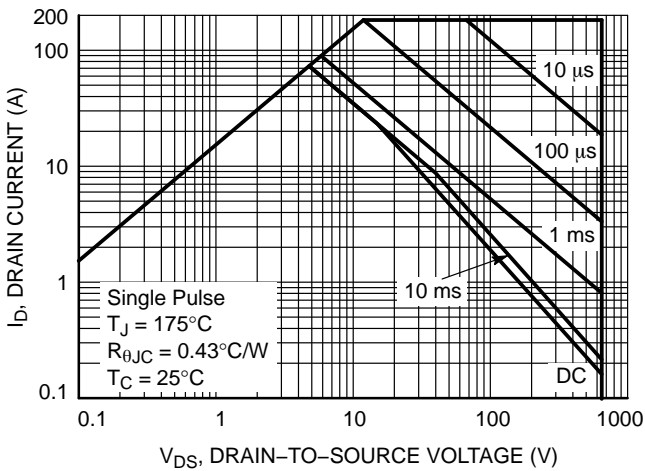


Figure 11. Safe Operating Area

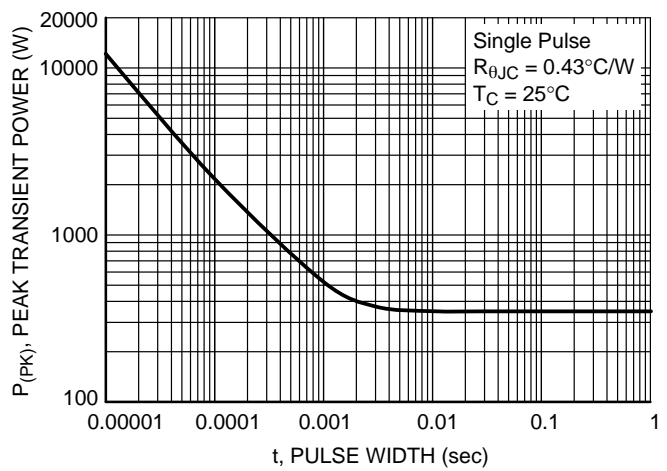


Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS

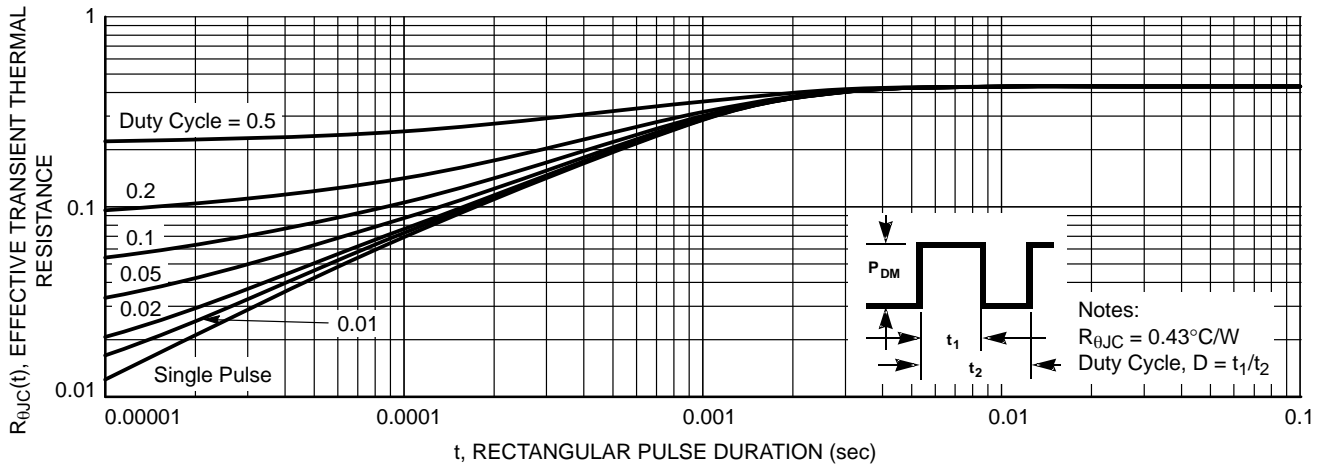


Figure 13. Transient Thermal Impedance

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTBL045N065SC1	H-PSOF8L	2000 / Tape & Reel

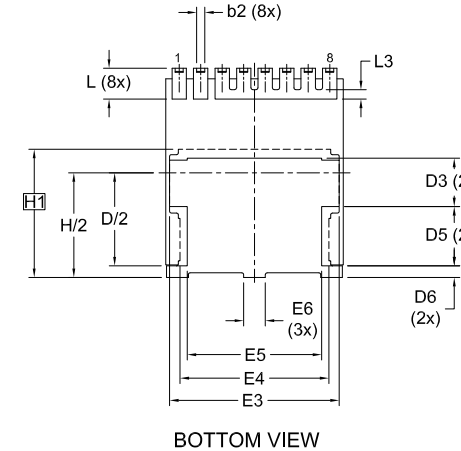
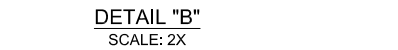
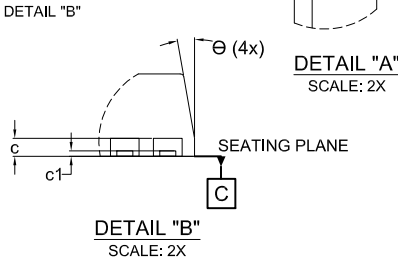
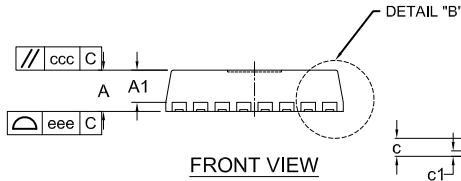
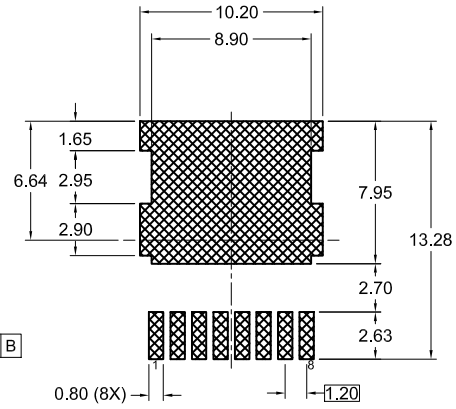
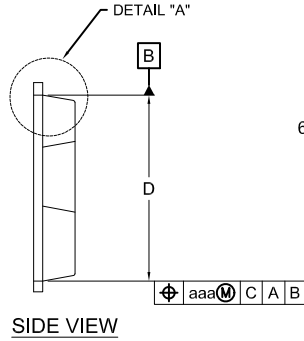
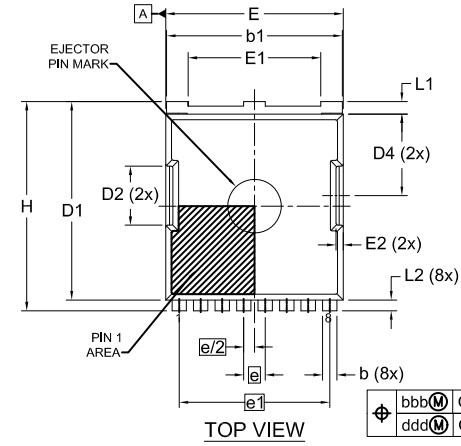
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

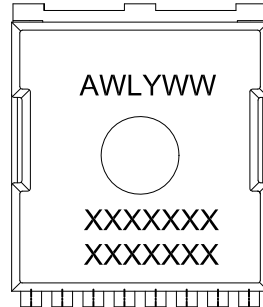


H-PSOF8L 9.90x11.68, 1.20P
CASE 100DC
ISSUE A

DATE 18 MAY 2023



GENERIC MARKING DIAGRAM*



A = ASSY LOCATION
WL = WAFER LOT CODE
Y = YEAR CODE
WW = WORK WEEK CODE
XXXXXXXX = DEVICE CODE
XXXXXXXX = DEVICE CODE

*THIS INFORMATION IS GENERIC.
PLEASE REFER TO DEVICE DATA SHEET FOR ACTUAL PART MARKING.

- NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE A.
 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 3. CONTROLLING DIMENSION: MILLIMETERS.
 4. COPLANARITY APPLIES TO THE EXPOSED WELL AS THE TERMINALS.
 5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
 6. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
c1	0.10	---	---
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	9.36	9.46	9.56

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E4	8.20	8.30	8.40
E5	7.40	7.50	7.60
E6	1.10	1.20	1.30
e	1.20 BSC		
e/2	0.60 BSC		
e1	8.40 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.63	1.73	1.83
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
theta	0°	---	12°
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

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